

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re: U.S. National Filing under)
35 U.S.C. §371 of International)
Application No. PCT/DE00/03293) PATENT

German Title: Mehrwertiger Magnetoresistiver)
Schreib/Lese-Speicher sowie Verfahren)
zum Beschreiben eines solchen Speichers)

English Translation: Multivalue Magnetoresistive Read/Write)
Memory and Method of Writing to and)
Reading from Such a Memory)

Applicant: Infineon Technologies, AG)

Inventors: Thewes, Roland)
Schwarzl, Siegfried)
Weber, Werner)

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20231

Sir:

PRELIMINARY AMENDMENT

In the above-entitled patent application, please amend the application as follows:

In the Claims

Please amend Claim No. 1 as follows:

- 1 1. (amended) A magnetoresistive read/write memory, with a plurality of
2 multivalue storage cells [(11)], each storage cell [(11)] having two intersecting electric
3 conductors [(12, 13)] and a layer system comprising magnetic layers located at the
4 intersection of [the] said electric conductors [(12, 13)], wherein [the] said layer system is
5 designed as a multilayer system [(30; 40)] with two or more magnetic layers [(31, 32;
6 41-45)], at least two, but a maximum of all [the] said magnetic layers [(31, 32; 41-45)]
7 hav[e]ing a magnetization direction [(33, 34; 46-50)] that can be set independently of one
8 another, [the] said magnetization direction [(33, 34; 46-50)] in [the] said individual layers
9 [(31, 32; 41-45)] [is] being changed [or can be changed] by the electric current flowing